



NTD4959NH-1G Information



For Reference Only

Part Number NTD4959NH-1G
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 9A IPAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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NTD4959NH-1G Specifications

Manufacturer Part Number NTD4959NH-1G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 9A (Ta), 58A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 11.5V Vgs(th) (Max) @ Id 2.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 44nC @ 11.5V Input Capacitance (Ciss) (Max) @ Vds 2155pF @ 12V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.3W (Ta), 52W (Tc) Rds On (Max) @ Id, Vgs 9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA		
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FET Type N-Channel Technology MOSFET (Metal Oxide) Jorain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Poerating Temperature Jordon Mounting Type Through Hole Supplier Device Package Package / Case N-Channel AUSFET (Metal Oxide) 30V 24V 24T 25V (25V (25V (25V (25V (25V (25V (25V (Package	TO-251-3 Short Leads, IPak, TO-251AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C9A (Ta), 58A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 11.5VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 11.5VInput Capacitance (Ciss) (Max) @ Vds2155pF @ 12VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta), 52W (Tc)Rds On (Max) @ Id, Vgs9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Series	-
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Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Porenting Temperature Poperating Temperature Supplier Device Package Package / Case PA (Ta), 58A (Tc) 9A (Ta), 58A (Tc) 1.5V 2.5V @ 250μA 44nC @ 11.5V 2155pF @ 12V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 11.5VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 11.5VInput Capacitance (Ciss) (Max) @ Vds2155pF @ 12VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta), 52W (Tc)Rds On (Max) @ Id, Vgs9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case 2.5V @ 250μA 2.5V @ 250μA 2.5V @ 250μA 44nC @ 11.5V 1.5V 1.5V 1.5V 1.2V -20V FET Feature -70 Power Dissipation (Max) 1.3W (Ta), 52W (Tc) 9 mOhm @ 30A, 10V -55°C ~ 175°C (TJ) Through Hole Supplier Device Package	Current - Continuous Drain (Id) @ 25°C	9A (Ta), 58A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2155pF @ 12V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 11.5V
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Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta), 52W (Tc)Rds On (Max) @ Id, Vgs9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	44nC @ 11.5V
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Power Dissipation (Max) Rds On (Max) @ Id, Vgs 9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	1.3W (Ta), 52W (Tc)
Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	9 mOhm @ 30A, 10V
Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

NTD4959NH-1G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTD4959NH-1G Payment Methods





















NTD4959NH-1G Shipping Methods













If you have any question about NTD4959NH-1G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com